

No.1785A

## 2SB1119/2SD1619

PNP/NPN Epitaxial Planar Silicon Transistors

LF Amp, Electronic Governor Applications

## **Features**

. Very small size making it easy to provide high-density, small-sized hybrid IC's

## (): 2SB1119

Absolute Maximum Ratings at Ta	=25 <sup>0</sup> C				unit
Collector to Base Voltage	$v_{CBO}$			(-)25	V
Collector to Emitter Voltage	VCEO			(-)25	V
Emitter to Base Voltage	VEBO			(-)5	V
Collector Current	IC			(-)1	A
Collector Current(Pulse)	$I_{CP}$			(-)2	Α
Collector Dissipation	P <sub>C</sub>			500	mW
		on ceramic board	$(250 \text{mm}^2 \times 0.$	.8mm)1.3	W
Junction Temperature	Τj			150	°C
Storage Temperature	Tstg		<del>-</del> 55	to +150	°C

## Electrical Characteristics at Ta=25°C

Rlectrical Characteristics	at Ta=250	C	min	typ	max	unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)20V,I <sub>E</sub> =0		(-)	0.1	$\mu \mathbf{A}$
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{EB}^{22} = (-)4V, I_{C}^{2} = 0$		(-)	0.1	$\mu \mathbf{A}$
DC Current Gain	hFE(1)	$V_{CE}^{DD} = (-)2V, I_{C} = (-)50mA$	100 🕷		560 <b>*</b>	
	hFE(2)	$V_{CE} = (-)2V, I_{C} = (-)1A$	40			
Gain-Bandwidth Product	fr	$V_{CE}^{2}=(-)10V, I_{C}=(-)50mA$		180		$\mathtt{MHz}$
C-E Saturation Voltage	VCE(sat)	$I_{C}=(-)500\text{mA}, I_{B}=(-)50\text{mA}$		0.1	0.3	V
	01(000)	ů ž	(-(	).15)(-	-0.7)	V
B-E Saturation Voltage	VBE(sat)	$I_{C}=(-)500mA, I_{B}=(-)50mA$	(-)	0.85(-)	1.2	V
C-B Breakdown Voltage	V(BR)CBO		-)25			V
C-E Breakdown Voltage	V(BR)CEO	$I_C = (-) 1 \text{mA}, R_{BE} = \infty$ (	-)25			V
E-B Breakdown Voltage	V(BR)EBO	$I_{E} = (-)10\mu\Lambda, I_{C} = 0$	(-)5			V
Output Capacitance	cop	$V_{CR} = (-)10V, f = 1MHz$		15		рF
				(25)		рF

\*: The 2SB1119/2SD1619 are classified by 50mA  $h_{\mbox{\scriptsize FE}}$  as follows:

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	100	R	200	140	S	280	200	T	400	280	U	560

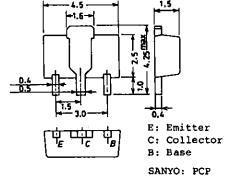
Marking 2SB1119:BB

2SD1619:DB

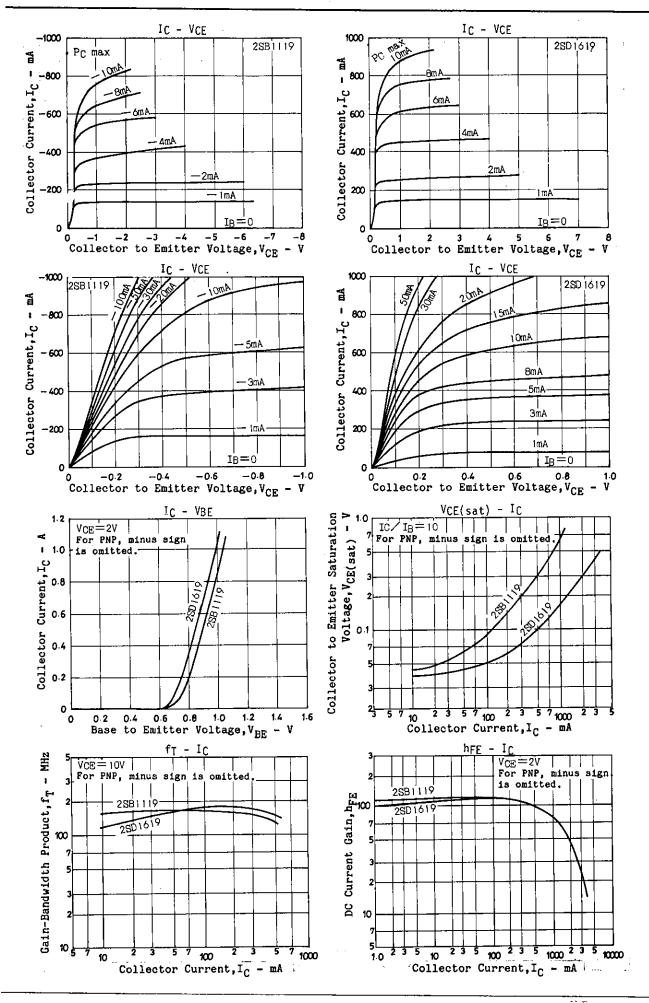
h<sub>FF</sub> rank :R,S,T,U

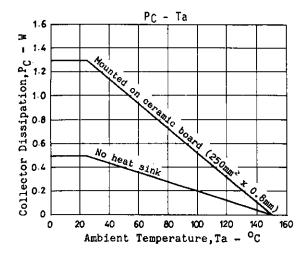
Package Dimensions 2038

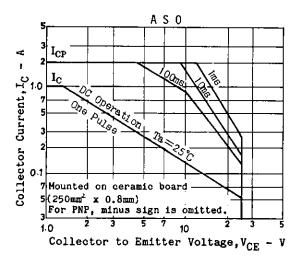
(unit:mm)



(Bottom View)







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